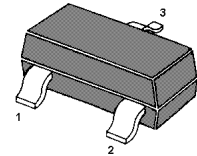
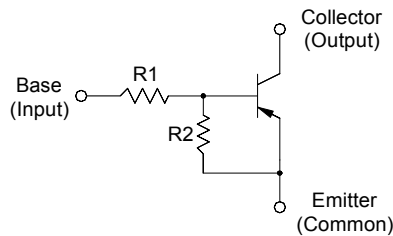


DTA114ECA PNP Silicon Epitaxial Planar Digital Transistor

FEATURES

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

MARKING: 14



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

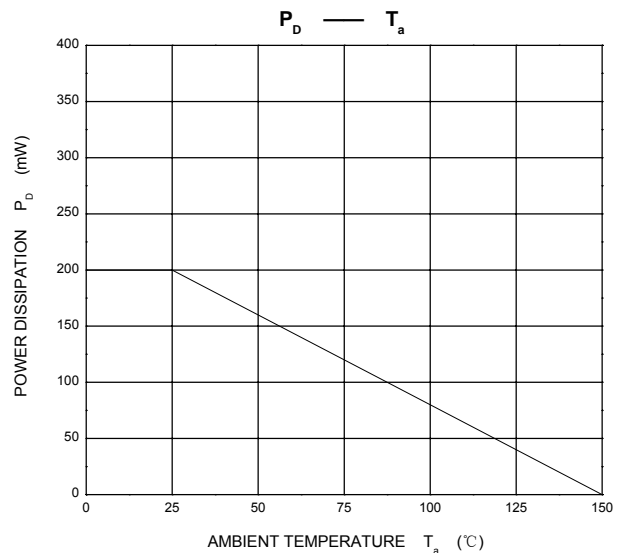
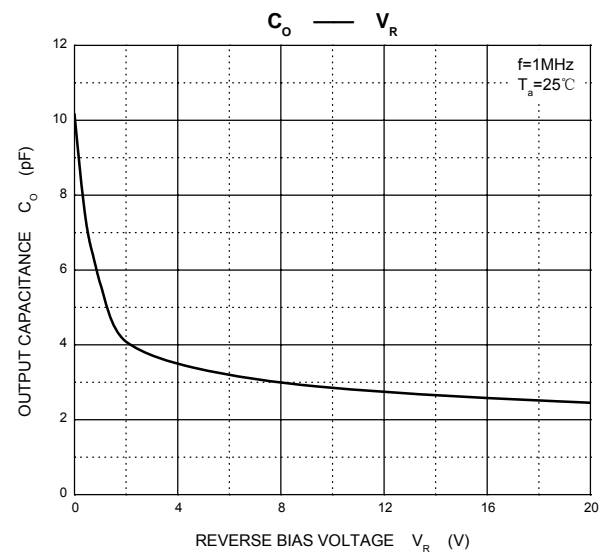
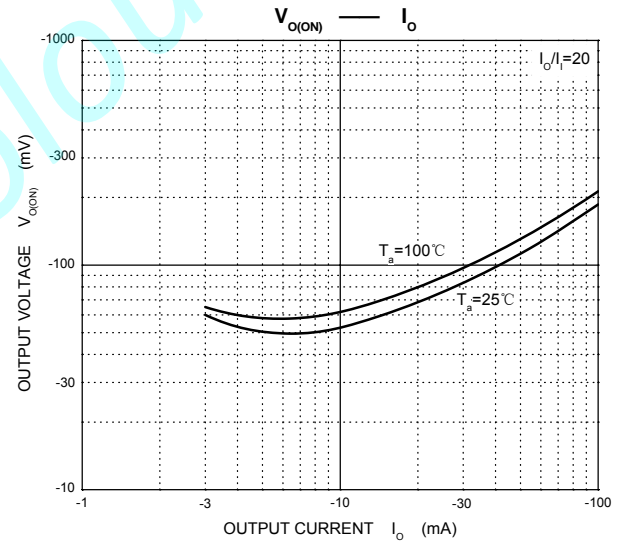
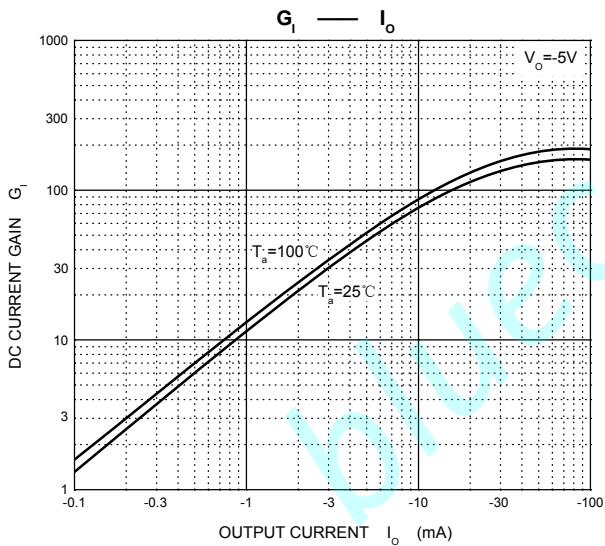
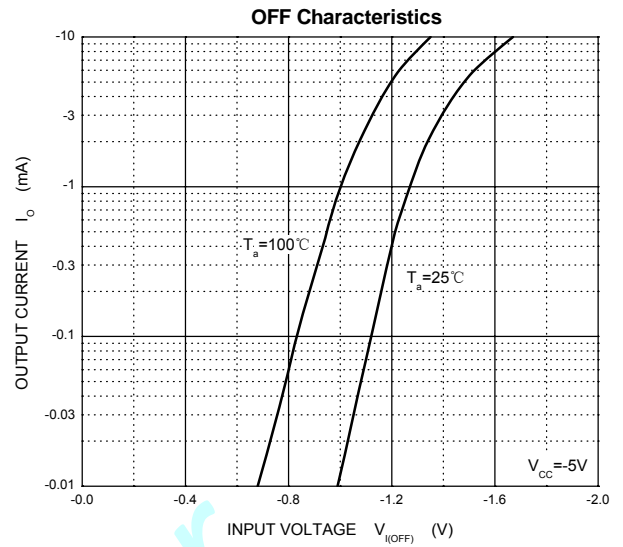
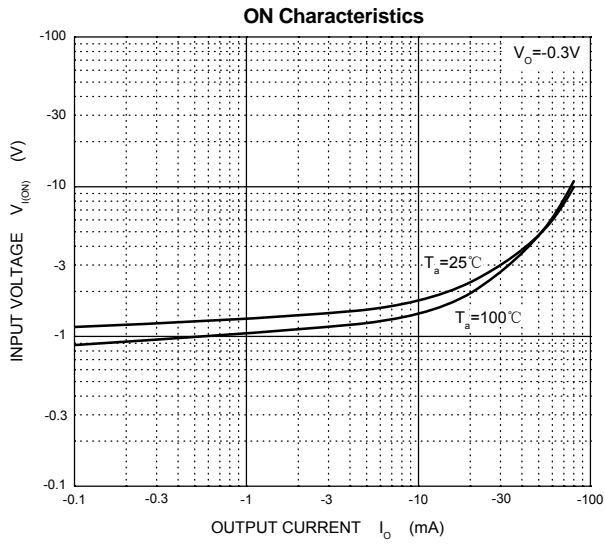
MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-50	V
V _{IN}	Input Voltage	-40~+10	V
I _O	Output Current	-50	mA
I _{CM}	Peak Collector Current	-100	mA
P _D	Power Dissipation	200	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input voltage	V _{I(off)}	V _{CC} =-5V, I _O =-100μA	-0.5			V
	V _{I(on)}	V _O =-0.3V, I _O =-10 mA			-3	V
Output voltage	V _{O(on)}	I _O /I _I =-10mA/-0.5mA			-0.3	V
Input current	I _I	V _I =-5V			-0.88	mA
Output current	I _{O(off)}	V _{CC} =-50V, V _I =0			-0.5	μA
DC current gain	G _I	V _O =-5V, I _O =-5mA	30			
Input resistance	R ₁		7	10	13	kΩ
Resistance ratio	R ₂ /R ₁		0.8	1	1.2	
Transition frequency	f _T	V _O =-10V, I _O =-5mA, f=100MHz		250		MHz

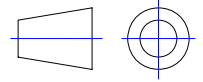
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20